Silicon NPN transistor in a TO-92 Plastic Package.

High f_T, low output capacitance, low base time constant and high gain, excellent noise characteristics.

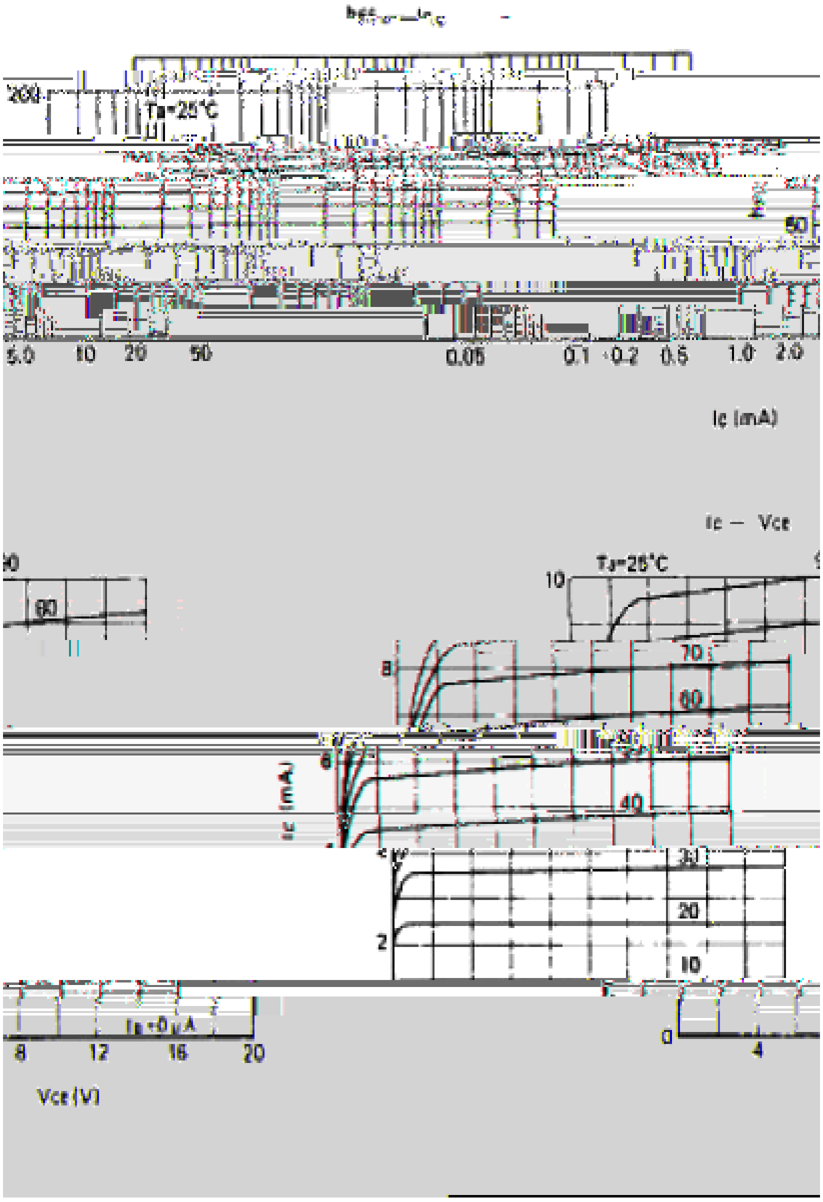
FM radio RF amplifier applications.

PIN1

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	25	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	4.0	V
Collector Current - Continuous	I_C	20	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

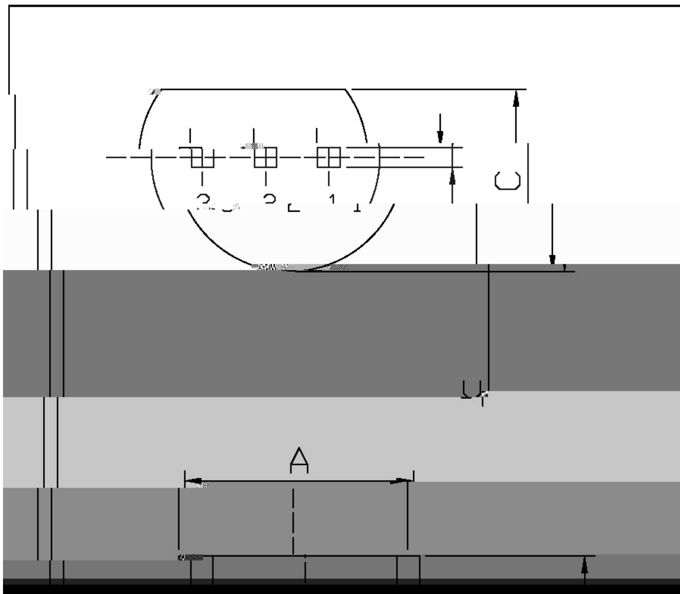
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=10 A	25			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA	20			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=10 A	4.0			V

Collector Cut-Off CurrenttorCVCut-O0003 Tc[EBO)8.3( )]TJ101.6re855.tter Breabr Cut-Of 9.3( )-220V94.3(09484.08 67

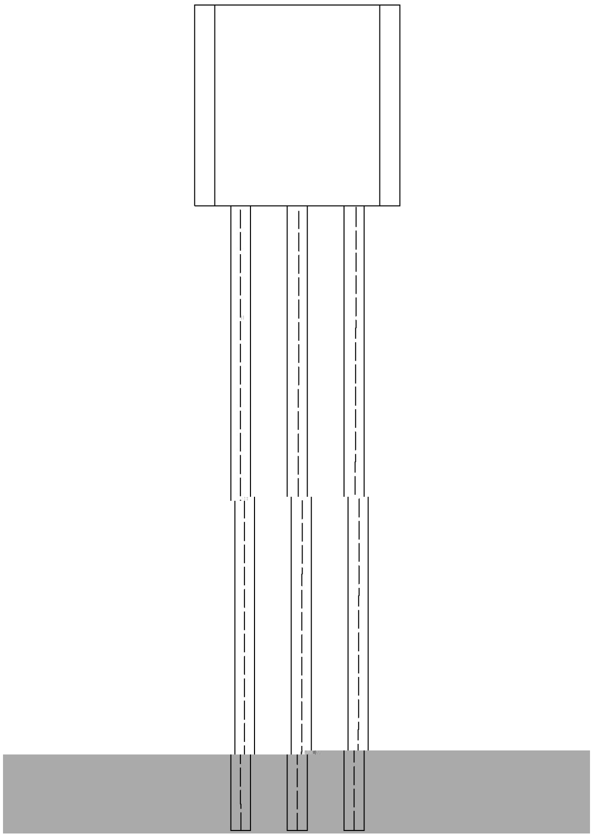

hFE — Ic
200
Ta=25°C
50
5.0
10
20
50
0.05
0.1
0.2
0.5
1.0
2.0
Ic (mA)
Ic — Vce
Ta=25°C
10
8
6
2
70
60
40
30
20
10
IB=0μA
0
4
8
12
16
20
Ic (mA)
Vce (V)

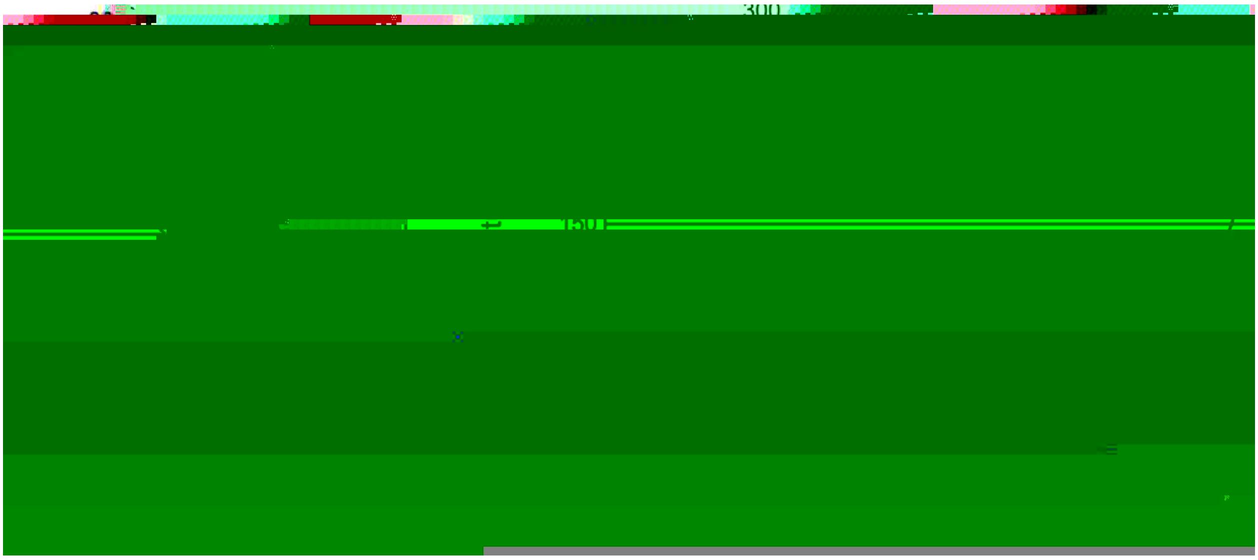
TO-92

Unit: mm



Symbol	Dimensions In Millimeters





1 25 150 60 90sec;

2 255 5 5 0.5sec;

3 2 10 /sec.

Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255 5 , Duration:5 0.5sec.

3. Cooling Speed: 2~10 /sec.

270 5 10 1 sec.

Temp:270±5 Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量	Dimension 包装尺寸 (unit: mm3)